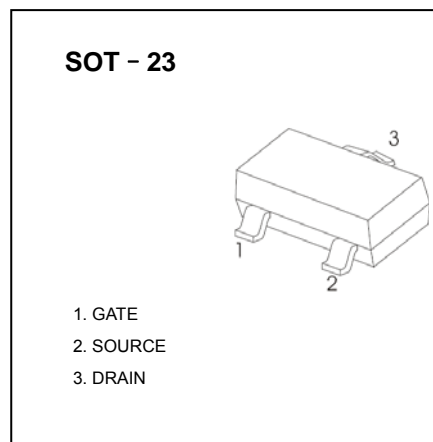


SOT-23 Plastic-Encapsulate MOSFETS

FDN338 P-Channel 20-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	112mΩ@-4.5V	-2.8A
	142mΩ@-2.5V	



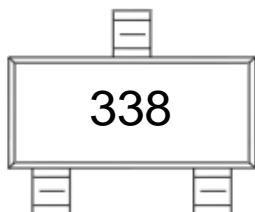
FEATURE

- TrenchFET Power MOSFET

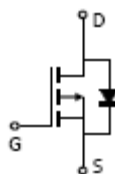
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±8	
Continuous Drain Current	I_D	-2.8	A
Pulsed Drain Current	I_{DM}	-10	
Continuous Source-Drain Diode Current	I_S	-0.72	
Maximum Power Dissipation	P_D	0.4	W
Thermal Resistance from Junction to Ambient($t \leq 5s$)	$R_{\theta JA}$	312.5	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55 ~ +150	

SOT-23 Plastic-Encapsulate MOSFETS

$T_a=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4		-1	
Gate-source leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -2.8A$		0.090	0.112	Ω
		$V_{GS} = -2.5V, I_D = -2.0A$		0.110	0.142	
Forward transconductance ^a	g_{fs}	$V_{DS} = -5V, I_D = -2.8A$		6.5		S
Dynamic^b						
Input capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		405		pF
Output capacitance	C_{oss}			75		
Reverse transfer capacitance	C_{rss}			55		
Total gate charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -3A$		5.5	10	nC
		$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -3A$		3.3	6	
Gate-source charge	Q_{gs}	$V_{DS} = -10V, V_{GS} = -2.5V, I_D = -3A$		0.7		
Gate-drain charge	Q_{gd}			1.3		
Gate resistance	R_g	$f = 1MHz$		6.0		Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10V,$ $R_L = 10\Omega, I_D = -1A,$ $V_{GEN} = -4.5V, R_g = 1\Omega$		11	20	ns
Rise time	t_r			35	60	
Turn-off delay time	$t_{d(off)}$			30	50	
Fall time	t_f			10	20	
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	$T_C = 25^{\circ}\text{C}$			-1.3	A
Pulse diode forward current ^a	I_{SM}				-10	
Body diode voltage	V_{SD}	$I_S = -0.7A$		-0.8	-1.2	V

Notes :

a.Pulse Test : Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.

b.Guaranteed by design, not subject to production testing.

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)